

CLAIM AMENDMENTS:

Claims 1 through 11 (canceled).

Claim 12 (currently amended): A semiconductor device, comprising:
a lower dielectric film;
an upper dielectric film formed in contact with the lower dielectric film;
a first interconnecting line having a first lower part formed in the lower dielectric film and a first upper part formed in the upper dielectric film, the first upper part making contact with the first lower part;
a second interconnecting line having a second lower part formed in the lower dielectric film and a second upper part formed in the upper dielectric film, the second upper part making contact with the second lower part;
wherein the first lower part and the second upper part have a first constant width;
and
the second lower part and the first upper part have a second constant width greater than the first constant width; and
the first interconnecting line and the second interconnecting line have a first height and the first upper part, the second upper part, the first lower part, and the second lower part have a second height equal to half the first height.

Claim 13 (previously presented): The semiconductor device of claim 12, wherein the first interconnecting line and the second interconnecting line are mutually adjacent.

Claim 14 (canceled).

Claim 15 (previously presented): The semiconductor device of claim 12, wherein the first upper part, the second upper part, the first lower part, and the second lower part are rectangular.

Claim 16 (previously presented): The semiconductor device of claim 15, wherein the first interconnecting line and the second interconnecting line have a cross-sectional T shape.

Claim 17 (canceled).

Claim 18 (withdrawn): A method of making a semiconductor device, comprising:
forming a lower dielectric film;
forming a first lower part of a first interconnecting line in the lower dielectric film;

forming a second lower part of a second interconnecting line in the lower dielectric film;

after said first lower part and said second lower part are formed in the lower dielectric film, forming upper dielectric film in contact with the lower dielectric film;

forming a first upper part of the first interconnecting line in the upper dielectric film, the first upper part making contact with the first lower part; and

forming a second upper part of the second interconnecting line in the upper dielectric film, the second upper part making contact with the second lower part;

wherein the first lower part and the second upper part have a first width;
and

the second lower part and the first upper part have a second width greater than the first width.

Claim 19 (new): A semiconductor device, comprising:
a lower dielectric film;
an upper dielectric film formed in contact with the lower dielectric film;
a first interconnecting line having a T-shape formed by a first vertical leg formed only in the lower dielectric film and a first horizontal leg formed only in the upper dielectric film, the first horizontal leg making contact with the first vertical leg;
a second interconnecting line having an inverted T-shape formed by a second horizontal leg formed only in the lower dielectric film and a second vertical

leg formed only in the upper dielectric film, the second vertical leg making contact with the second horizontal leg;

wherein the first vertical leg and the second vertical leg have a same width, which is constant over an entire length of the respective vertical legs;

the second horizontal leg and the first horizontal leg have a same width, which is constant along the respective horizontal legs, the width of the horizontal legs being greater than the width of the vertical legs; and

the first interconnecting line and the second interconnecting line have a first height, and the first vertical leg, the second vertical leg, the first horizontal leg, and the second horizontal leg each have a second height equal to half the first height, the heights being measured in a vertical direction, the widths being measured in a horizontal direction.